

July 23, 2003
News Release 03-065
Inv. No. 701-TA-431 (Final)

DRAMs AND DRAM MODULES FROM KOREA INJURE U.S. INDUSTRY, SAYS ITC

The United States International Trade Commission (ITC) today determined that a U.S. industry is materially injured or threatened with material injury by reason of imports of DRAMs and DRAM Modules from Korea that the U.S. Department of Commerce has determined are subsidized.

Chairman Deanna Tanner Okun, Vice Chairman Jennifer A. Hillman, and Commissioner Stephen Koplan voted in the affirmative. Commissioner Marcia E. Miller did not participate in this investigation.

As a result of the Commission's affirmative determination, the U.S. Department of Commerce will issue a countervailing duty order on imports of DRAMs and DRAM Modules from Korea.

The Commission's public report *DRAMs and DRAM Modules from Korea* (Investigation No. 701-TA-431 (Final), USITC Publication 3617, August 2003) will contain the views of the Commission and information developed during the investigation.

Copies may be obtained after August 25, 2003, by calling 202-205-1809 or from the Office of the Secretary, 500 E Street SW, Washington, DC 20436. Requests may also be made by fax to 202- 205-2104.

UNITED STATES INTERNATIONAL TRADE COMMISSION
Office of Industries
Washington, DC 20436

FACTUAL HIGHLIGHTS

DRAMs and DRAM Modules from Korea
Investigation No. 701-TA-431 (Final)

Product Description: The imported products subject to this investigation are dynamic random access memory semiconductors ("DRAMs") of various types from Korea, whether assembled or unassembled. Assembled DRAMs include all package types. Unassembled DRAMs include processed wafers, uncut die, and cut die. Also included are memory modules containing DRAMs from Korea. A memory module is a collection of DRAMs, the sole function of which is memory. Memory modules include single in-line processing modules ("SIPs"), single in-line memory modules ("SIMMs"), dual in-line memory modules ("DIMMs"), small outline dual in-line memory modules ("SODIMMs"), Rambus in-line memory modules ("RIMMs"), and memory cards or other collections of DRAMs, whether unmounted or mounted on a circuit board. Also included are video random access memory ("VRAM"), and synchronous graphics RAM ("SGRAM"), as well as various types of DRAMs, including fast page-mode ("FPM"), extended data-out ("EDO"), burst extended data-out ("BEDO"), synchronous dynamic RAM ("SDRAM"), Rambus DRAM ("RDRAM"), and Double Data Rate DRAM ("DDR DRAM"). DRAMs and DRAM modules are used as the main memory in a variety of electronics products including computers and computer peripherals, telecommunications equipment, networking equipment, and consumer electronics devices. By far, the largest end use for DRAMs and DRAM modules is computer equipment.

Status of Proceedings:

1. Type of investigation: Final countervailing.
2. Petitioner: Micron Technology, Inc., Boise, ID.
3. Investigation instituted by the USITC: November 1, 2002.
4. Hearing: June 24, 2003.
5. USITC vote: July 23, 2003.
6. USITC determination to the U.S. Department of Commerce: August 4, 2003.

U.S. Industry:

1. Number of producers in 2002: 6.
2. Location of producers' plants: Manassas, VA; Eugene, OR; Sandston, VA; Fountain Valley, CA; Boise, ID; Austin, TX.
3. Employment of production and related workers in 2002: (1)
4. Apparent U.S. consumption in 2002: \$4.6 billion
5. Ratio of the value of total U.S. shipments of foreign DRAM products to total U.S. consumption in 2002: 72 percent.

U.S. Imports:

1. From the subject country during 2002: (1)
2. From other countries during 2002: (1)
3. Leading source during 2002: Korea.

(1) Withheld to avoid disclosure of business proprietary information.

